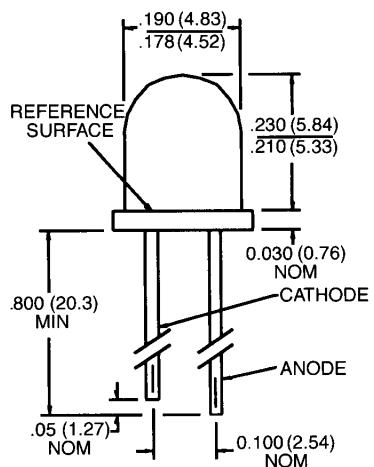




AIGaAs INFRARED EMITTING DIODE

QED422/423

PACKAGE DIMENSIONS

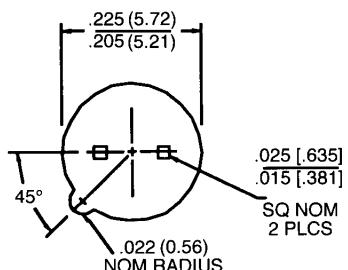


DESCRIPTION

The QED42X is an 880nm AIGaAs LED encapsulated in a clear, purple tinted, plastic TO-46 package.

FEATURES

- Tight production E_θ distribution.
- Steel lead frames for improved reliability in solder mounting.
- Good optical-to-mechanical alignment.
- Wide emission angle.
- Mechanical and wavelength matched to QSD42X series phototransistor.
- Plastic package color allows easy recognition from phototransistor.
- High irradiance level.



ST2135

NOTES:

1. DIMENSIONS ARE IN INCHES (mm).
2. TOLERANCE IS $\pm .010$ (.25)
UNLESS OTHERWISE SPECIFIED.
3. TAB DENOTES CATHODE.



AIGaAs INFRARED EMITTING DIODE

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Specified)

Storage Temperature	-40°C to + 100°C
Operating Temperature	-40°C to + 100°C
Soldering:	
Lead Temperature (Iron)	240°C for 5 sec. ^(2,3,4,5)
Lead Temperature (Flow)	260°C for 10 sec. ^(2,3,5)
Continuous Forward Current	100 mA
Reverse Voltage	5.0 Volts
Power Dissipation	200 mW ⁽¹⁾

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless Otherwise Specified)

(All measurements made under pulse conditions.)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
Forward Voltage	V_F	—	—	1.70	V	$I_F = 20 \text{ mA}$
Reverse Leakage Current	I_R	—	—	10	μA	$V_R = 5.0 \text{ V}$
Peak Emission Wavelength	λ_p	—	880	—	nm	$I_F = 20 \text{ mA}$
Emission Angle at $1/2$ Power	θ	—	± 35	—	Degrees	
Radiant Incidence QED422	E_o	0.05	—	0.25	mW/10° Cone	$I_F = 20 \text{ mA}^{(6,7)}$
Radiant Incidence QED234	E_o	0.10	—	—	mW/10° Cone	$I_F = 20 \text{ mA}^{(6,7)}$

NOTES

1. Derate power dissipation linearly 2.67 mW/°C above 25°C.
2. RMA flux is recommended.
3. Methanol or Isopropyl alcohols are recommended as cleaning agents.
4. Soldering iron tip $1/8"$ (1.6 mm) minimum from housing.
5. As long as leads are not under any stress or spring tension.
6. Measurement is taken at the end of a single 100 μsec pulse.
7. E_o is a measurement of the average apertured radiant energy incident upon a sensing area 0.444" (11.3 mm) in diameter, perpendicular to and centered on the mechanical axis of the lens, and 2.54" (64.4 mm) from the measurement surface. E_o is not necessarily uniform within the measurement area.